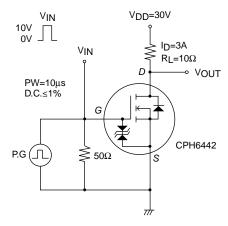
CPH6442

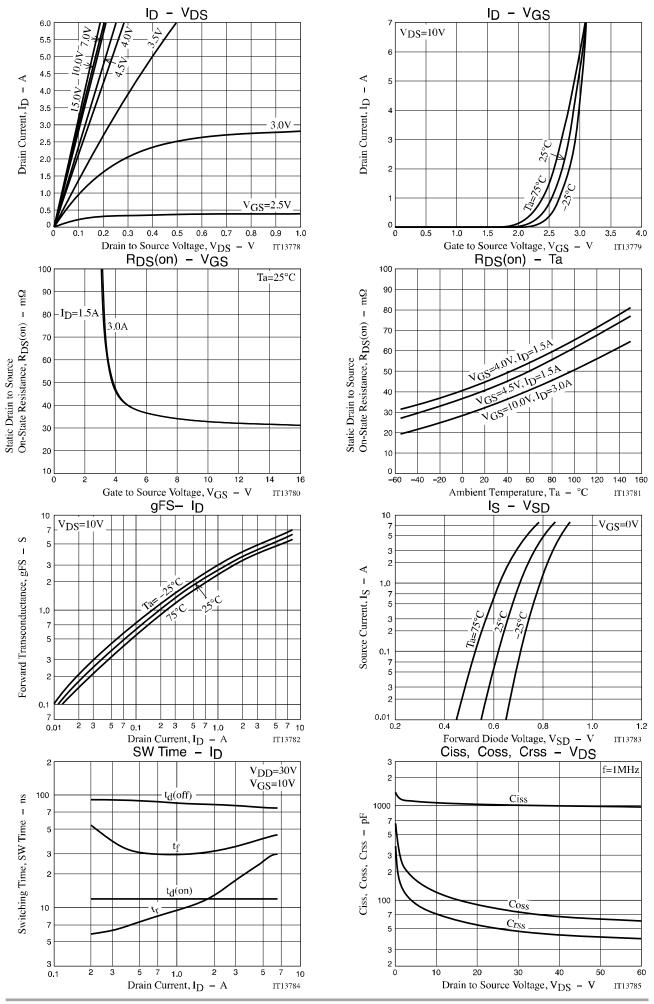
Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Value			Unit
Parameter		Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	60			٧
Zero-Gate Voltage Drain Current IDSS		V _{DS} =60V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA 1.2			2.6	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =3A 2.6		4.4		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =3A, V _{GS} =10V		33	43	mΩ
	R _{DS} (on)2	I _D =1.5A, V _{GS} =4.5V		42	59	mΩ
	R _{DS} (on)3	I _D =1.5A, V _{GS} =4V		46	65	mΩ
Input Capacitance	Ciss			1040		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		90		pF
Reverse Transfer Capacitance	Crss			55		pF
Turn-ON Delay Time	t _d (on)			12		ns
Rise Time	t _r	Out and Total City II		18		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		80		ns
Fall Time	t _f	1		35		ns
Total Gate Charge	Qg			20		nC
Gate to Source Charge	Qgs	V _{DS} =30V, V _{GS} =10V, I _D =6A		3.0		nC
Gate to Drain "Miller" Charge	Qgd]		4.2		nC
Forward Diode Voltage	V _{SD}	I _S =6A, V _{GS} =0V 0.82		1.2	V	

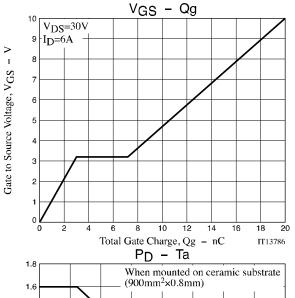
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

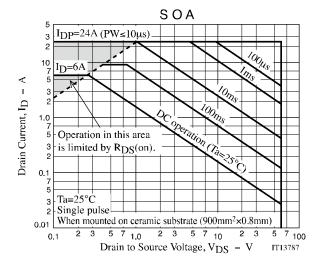
Switching Time Test Circuit

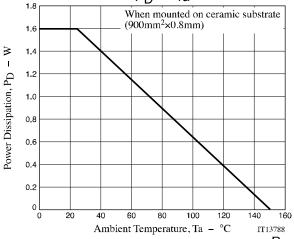


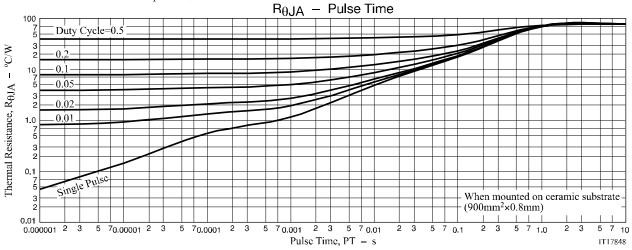


CPH6442









Package Dimensions

CPH6442-TL-E / CPH6442-TL-W

CPH₆

CASE 318BD ISSUE O

Unit: mm

1: Drain

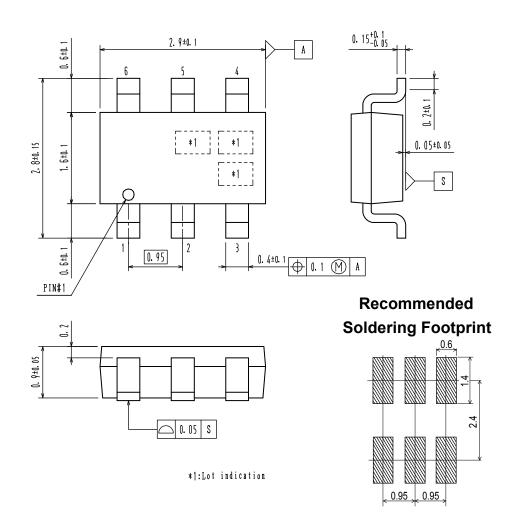
2: Drain

3: Gate

4 : Source

5: Drain

6: Drain



ORDERING INFORMATION

Device	Package	Shipping	Note	
CPH6442-TL-E	CPH6, SC-74	3,000 pcs. / Tape & Reel	Pb-Free	
CPH6442-TL-W	SOT-26, SOT-457	5,000 pcs. / Tape & Neel	Pb-Free and Halogen Free	

Note on usage: Since the CPH6442 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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